

Isc N-Channel MOSFET Transistor

IPB027N10N5

• FEATURES

- With To-263(D2PAK) package
- Low input capacitance and gate charge
- Low gate input resistance
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

• APPLICATIONS

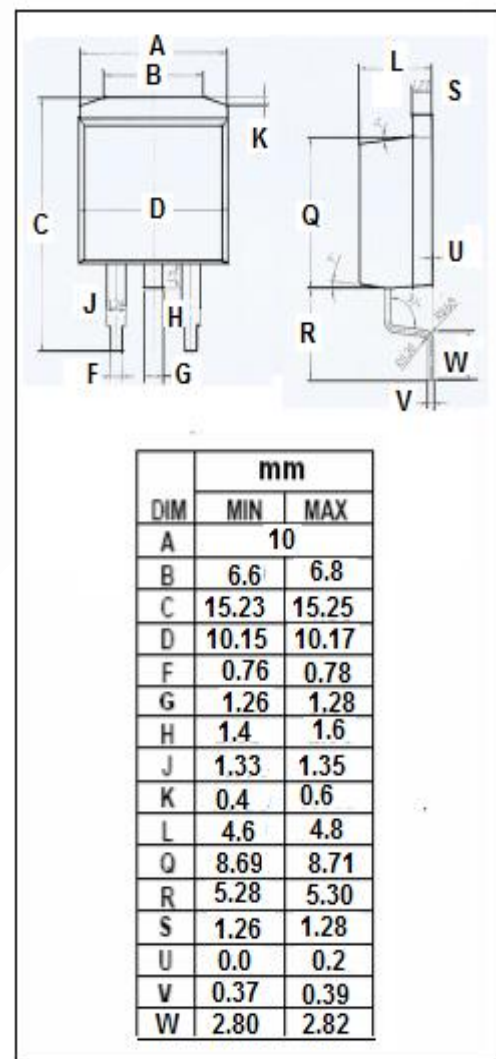
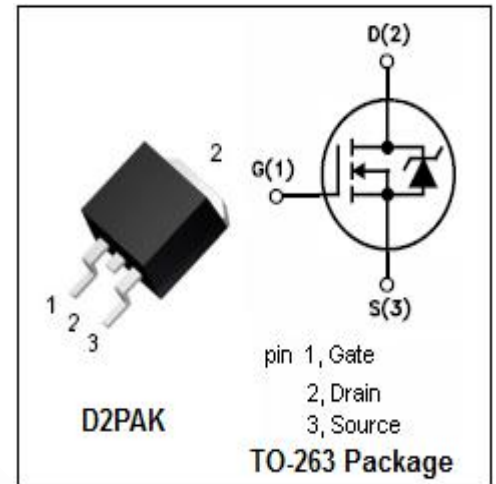
- Switching applications

• ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{DSS}	Drain-Source Voltage	100	V
V _{GSS}	Gate-Source Voltage	±20	V
I _D	Drain Current-Continuous T _c =25°C T _c =100°C	120	A
I _{DM}	Drain Current-Single Pulsed	480	A
P _D	Total Dissipation @T _c =25°C	250	W
T _{ch}	Max. Operating Junction Temperature	175	°C
T _{stg}	Storage Temperature	-55~175	°C

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th(ch-c)}	Channel-to-case thermal resistance	0.6	°C/W
R _{th(ch-a)}	Channel-to-ambient thermal resistance	40	°C/W



Isc N-Channel MOSFET Transistor**IPB027N10N5****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V; I_D=1mA$	100			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=5V; I_D=0.275mA$	2.2		3.8	V
$R_{DS(on)}$	Drain-Source On-Resistance	$V_{GS}=10V; I_D=100A$		2.4	2.7	$m\Omega$
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V; V_{DS}=0V$			± 0.1	μA
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=100V; V_{GS}=0V; T_j=25^{\circ}\text{C}$ $V_{DS}=100V; V_{GS}=0V; T_j=125^{\circ}\text{C}$			5 100	μA
V_{SDF}	Diode forward voltage	$I_{SD}=100A, V_{GS}=0V$		0.92	1.2	V